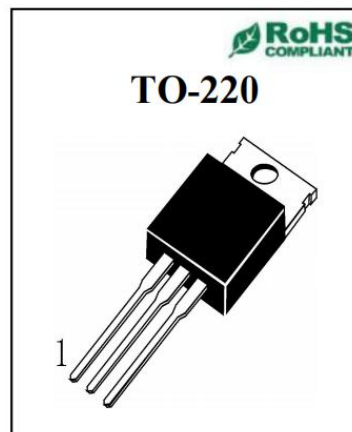


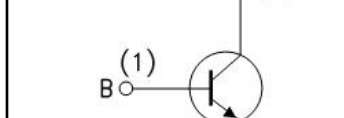
NPN/PNP Complementary Silicon Power Transistors

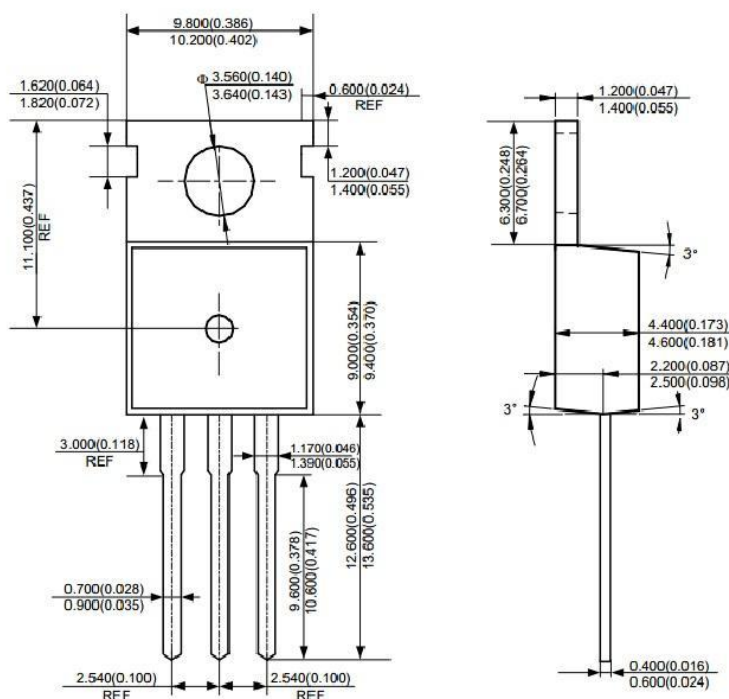
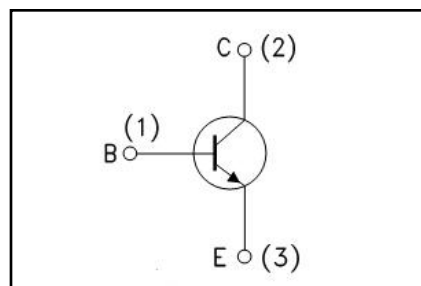
◆ Features:

- ✧ High efficiency, low deviation
高效率，低偏差
- ✧ Small input impedance, low consumption of power
输入阻抗小，功耗低
- ✧ Resistant of high temperature, high humidity
抗高温、高湿
- ✧ Good stability, reliability
稳定性好，可靠性高



◆ Applications

- ✧ Audio amplifier
音频放大器
 - ✧ Switching applications
开关应用
 - ✧ Complement to Type A940(PNP)
与 A940(PNP)互补应用
 - ✧ Recommend for 25W high fidelity audio frequency amplifier output stage applications
推荐用于 25W 高保真音频放大器输出级应用
- 



◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	170	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	150	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	7	V
Ic	Collector Current-Continuous 集电极连续电流	1.5	A
PC	Collector Power Dissipation 耗散功率	25	W
Tj	Max.Operating junction temperature 最大结温	150	°C
Tstg	Storage Temperature 存储温度	-55 ~ +125	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I _{CBO}	Collector Cutoff Current 集电极截止电流		--	10	μA	V _{CE} =180V, I _B =0
I _{EBO}	Emitter Cutoff Current 发射极截止电流		--	10	μA	V _{EB} =7V, I _C =0
BV _{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	150			V	I _C =2mA, I _B =0
V _{CE(sat)}	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压			1.0	V	I _C =5A, I _B =0.5A
h _{FE}	DC Current Gain(Note 1) 直流电流增益	70	--	200		I _C =0.5A, V _{CE} =5V

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.